# Power management (dual transistors) EMF23/UMF23N

2SA1774and DTC114E are housed independently in a EMT6 or UMT6 package.

## Application

Power management circuit

#### Features

1) Power switching circuit in a single package.

2) Mounting cost and area can be cut in half.

## Structure

Silicon epitaxial planar transistor

## •Equivalent circuits



## •External dimensions (Units : mm)



#### •Package, marking, and packaging specifications

Туре	EMF23	UMF23N	
Package	EMT6	UMT6	
Marking	F23	F23	
Code	T2R	TR	
Basic ordering unit(pieces)	8000	3000	

## Transistors

## ●Absolute maximum ratings (Ta=25°C)

## Tr1

Parameter	Symbol	Limits	Unit
Collector-base voltage	Vсво	-60	V
Collector-emitter voltage	Vceo	-50	V
Emitter-base voltage	Vebo	-6	V
Collector current	lc	-150	mA
Collector power dissipation	Pc	150 (TOTAL)	mW *
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

\* 120mW per element must not be exceeded.

## DTr2

Parameter	Symbol	Limits	Unit
Supply voltage	Vcc	50	V
Input voltage	Vin	-10~+40	V
Collector current	lc	100	mA *1
Output current	lo	50	mA
Power dissipation	Pc	150(TOTAL)	mW *2
Junction temperature	Tj	150	°C
Range of storage temperature	Tstg	-55 to +150	°C

\*1 Characteristics of built-in transistor. \*2 120mW per element must not be exceeded. Each terminal mounted on a recommended land.

## ●Electrical characteristics (Ta=25°C)

#### Tr1

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	-60	-	-	V	Ic=-50μA
Collector-emitter breakdown voltage	BVCEO	-50	-	-	V	Ic=-1mA
Emitter-base breakdown voltage	ВVево	-6	-	-	V	I <sub>E</sub> =-50μA
Collector cutoff current	Ісво	-	-	-0.1	μΑ	V <sub>CB</sub> =-60V
Emitter cutoff current	Іево	-	-	-0.1	μΑ	VEB=-6V
Collector-emitter saturation voltage	VCE (sat)	-	_	-0.5	V	Ic/I <sub>B</sub> =-50mA/-5mA
DC current transfer ratio	hfe	180	-	390	-	Vce=-6V, Ic=-1mA
Transition frequency	fт	_	140	-	MHz	Vce=-12V, Ie=2mA, f=100MHz
Output capacitance	Cob	_	4	5	pF	V <sub>CB</sub> =-12V, I <sub>E</sub> =0A, f=1MHz

## DTr2

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Input voltage	VI(off)	-	-	0.5	V	Vcc=5V, Io=100μA
	VI(on)	3	-	-		Vo=0.3V, Io=10mA
Output voltage	VO(on)	-	0.1	0.3	V	lo/l=10mA/0.5mA
Input current	h	-	-	0.88	mA	Vi=5V
Output current	IO(off)	-	-	0.5	μΑ	Vcc=50V, Vi=0V
DC current gain	Gi	30	-	-	-	Vo=5V, Io=5mA
Input resistance	R1	7	10	13	kΩ	_
Resistance ratio	R2/R1	0.8	1	1.2	-	-
Transition frequency	fт	-	250	-	MHz	Vce=10V, Ie=-5mA, f=100MHz

Transition frequency of the device



## Transistors

#### •Electrical characteristic curves



# Transistors

DTr2





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